

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TRW53601** is Designed for General Purpose Oscillator Applications up to 2.3 GHz.

FEATURES:

- Diffused Ballast Resistors
- **Omnigold™** Metalization System
- Common Emitter

MAXIMUM RATINGS

I_C	400 mA
V_{CES}	50 V
P_{DISS}	3.0 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	31 °C/W

PACKAGE STYLE

DIM	MILLIMETER	TOL	INCHES	TOL
A	20.32	.13	.800	.005
B	14.27	.13	.562	.005
C	18.03	MIN	.710	MIN
D	5.84	.13	.230	.005
E	3.05	.13	.120	.005
F	1.27 x 45°	.13	.005x45°	.005
G	5.84	.13	.230	.005
H	4.57	REF	.180	REF
I	0.13	.02	.005	.001
J	3.30	.13	.130	.005
K	1.52	.13	.060	.005
M	1.27	.13	.050	.005
N	3.30 DIA	.13	.130 DIA	.005

1 = COLLECTOR 2 = EMITTER 3 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 10 mA	20			V
BV_{CES}	I _C = 10 mA	50			V
BV_{CBO}	I _C = 1.0 mA	45			V
BV_{EBO}	I _E = 250 μA	3.5			V
I_{CBO}	V _{CB} = 28 V			0.25	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	15		120	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz			3.5	pF
P_O	V _{CE} = 20 V I _E = 120 mA f = 2.0 GHz	.8			W
IMD	V _{CE} = 20 V I _E = 120 mA f = 2.0 GHz P _{IN} = .100 W		-30		dB
G_P		8.5	9.5		dB
VSWR		∞			